

4N22A

4N23A JAN, JANTX, JANTXV, AND JANS SINGLE CHANNEL OPTOCOUPPLERS

4N24A



07/07/03

Features:

- Qualified to MIL-PRF-19500/486
- Collector is electrically isolated from the case
- Overall current gain: 1.5 typical (4N24A)
- Base lead provided for conventional transistor biasing
- Rugged package
- High gain, high voltage transistor
- +1kV electrical isolation

Applications:

- Eliminate ground loops
- Level shifting
- Line receiver
- Switching power supplies
- Motor control

DESCRIPTION

A Gallium Aluminum Arsenide (GaAlAs) infrared LED and a high gain N-P-N silicon phototransistor packaged in a hermetically sealed metal case. The 4N22A, 4N23A, and 4N24A differ from the 4N22, 4N23, and 4N24 only in that the collector of the transistor is isolated from the case. The **4N22A**, **4N23A** and **4N24A** can be tested to customer specifications.

***ABSOLUTE MAXIMUM RATINGS**

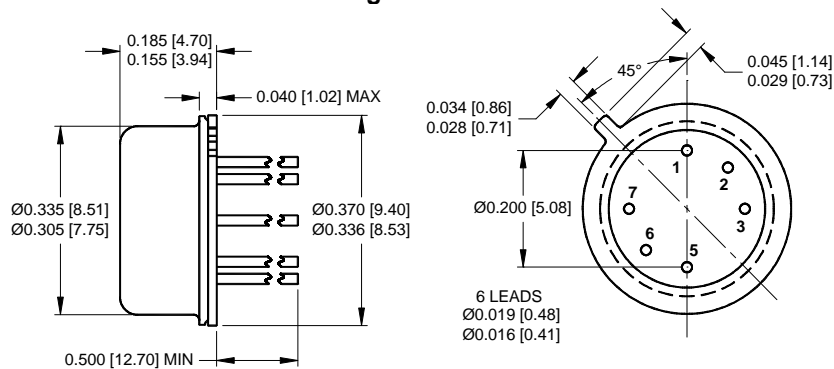
Input to Output Voltage	±1kV
Emitter-Collector Voltage	4V
Collector-Emitter Voltage	35V
Collector-Base Voltage	35V
Reverse Input Voltage	2V
Input Diode Continuous Forward Current at (or below) 25°C Free-Air Temperature (see note 1)	40mA
Peak Forward Input Current (Value applies for $t_w \leq 1\mu s$ PRR < 300 pps)	1A
Continuous Collector Current	50mA
Continuous Transistor Power Dissipation at (or below) 25°C Free-Air Temperature (see Note 2)	300mW
Storage Temperature	-65°C to +125°C
Operating Free-Air Temperature Range	-55°C to +125°C
Lead Solder Temperature (10 seconds max., 1/16" from case)	240°C

Notes:

1. Derate linearly to 125°C free-air temperature at the rate of 0.40 mA/°C above 65°C.
2. Derate linearly to 125°C free-air temperature at the rate of 5 mW/°C above 65°C.

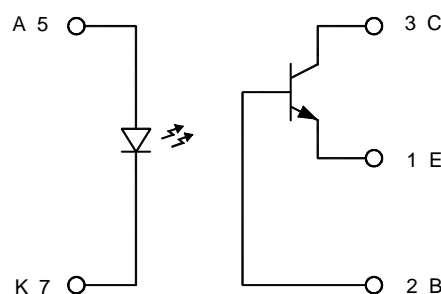
- JEDEC registered data

Package Dimensions



ALL LINEAR DIMENSIONS ARE IN INCHES [MILLIMETERS].

Schematic Diagram



THE COLLECTOR OF THE TRANSISTOR IS ISOLATED FROM THE CASE.

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***ELECTRICAL CHARACTERISTICS INPUT LED** $T_A = 25^\circ\text{C}$ Unless otherwise specified

PARAMETER	SYMBOL	MIN	MAX	UNITS	TEST CONDITIONS	NOTE
Input Diode Static Reverse Current	I_R		100	nA	$V_R = 2V$	
Input Diode Static Forward Voltage	V_F	1	1.5	V	$I_F = 10\text{mA}$	
		0.8	1.3			
		0.7	1.2			

***OUTPUT TRANSISTOR** $T_A = 25^\circ\text{C}$ Unless otherwise specified

PARAMETER	SYMBOL	MIN	MAX	UNITS	TEST CONDITIONS	NOTE
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	35		V	$I_C = 100\mu\text{A}, I_E = 0, I_F = 0$	
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	35		V	$I_C = 1\text{mA}, I_B = 0, I_F = 0$	
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	7		V	$I_B = 0, I_E = 100\mu\text{A}, I_F = 0$	

***COUPLED CHARACTERISTICS** $T_A = 25^\circ\text{C}$ Unless otherwise specified

PARAMETER	SYMBOL	MIN	MAX	UNITS	TEST CONDITIONS	NOTE
On State Collector Current	$I_{C(ON)}$	0.15		mA	$V_{CE} = 5V, I_B = 0, I_F = 2\text{mA}$	
		0.2				
		0.4				
On State Collector Current	$I_{C(ON)}$	2.5		mA	$V_{CE} = 5V, I_B = 0, I_F = 10\text{mA}$	
		6				
		10				
On State Collector Current	$I_{C(ON)}$	1		mA	$V_{CE} = 5V, I_B = 0, I_F = 10\text{mA}$	
-55°C		2.5				
		4				
On State Collector Current	$I_{C(ON)}$	1		mA	$V_{CE} = 5V, I_B = 0, I_F = 10\text{mA}$	
+100°C		2.5				
		4				
Off State Collector Current	$I_{C(OFF)}$		100	nA	$V_{CE} = 20V, I_B = 0, I_F = 0\text{mA}$	
+25°C			100	μA	$V_{CE} = 20V, I_B = 0, I_F = 0\text{mA}$	
Off State Collector Current	$I_{C(OFF)}$		100	μA	$V_{CE} = 20V, I_B = 0, I_F = 0\text{mA}$	
+100°C			100	μA	$V_{CE} = 20V, I_B = 0, I_F = 0\text{mA}$	
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$		0.3	V	$I_C = 2.5\text{mA}, I_B = 0, I_F = 20\text{mA}$	
			0.3	V	$I_C = 5\text{mA}, I_B = 0, I_F = 20\text{mA}$	
			0.3	V	$I_C = 10\text{mA}, I_B = 0, I_F = 20\text{mA}$	
Input to Output Resistance	R_{I-O}	10^{11}		Ω	$V_{IN-OUT} = 1\text{kV}$	1
Input to Output Capacitance	C_{I-O}		5	pF	$F = 1\text{MHz}, V_{IN-OUT} = 1\text{kV}$	1
Rise Time	t_r		15	μs	$V_{CC} = 10V, I_F = 10\text{mA}, R_L = 100\Omega$	
			15	μs		
			20	μs		
Fall Time	t_f		15	μs	$V_{CC} = 10V, I_F = 10\text{mA}, R_L = 100\Omega$	
			15	μs		
			20	μs		

NOTES:

- These parameters are measured between all phototransistor leads shorted together and with both input diode leads shorted together.

RECOMMENDED OPERATING CONDITIONS:

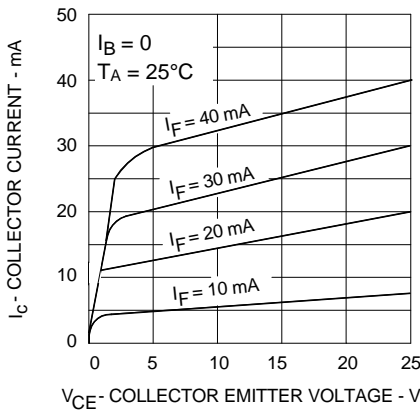
PARAMETER	SYMBOL	MIN	MAX	UNITS
Input Current, Low Level	I_{FL}	0	1	μA
Input Current, High Level	I_{FH}	2	10	mA
Supply Voltage	V_{CC}	5	10	V

SELECTION GUIDE

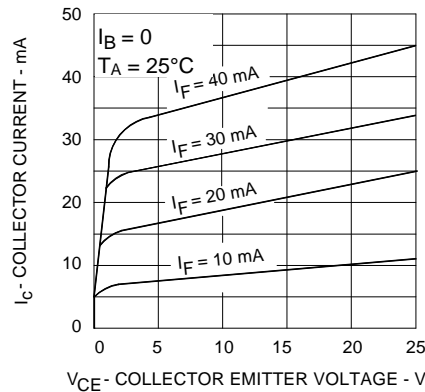
PART NUMBER	PART DESCRIPTION
4N22A	Commercial
4N23A	Commercial
4N24A	Commercial
JAN4N22A	JAN Screened
JAN4N23A	JAN Screened
JAN4N24A	JAN Screened
JANTX4N22A	JANTX Screened
JANTX4N23A	JANTX Screened
JANTX4N24A	JANTX Screened
JANTXV4N22A	JANTXV Screened
JANTXV4N23A	JANTXV Screened
JANTXV4N24A	JANTXV Screened
JANS4N22A	JANS Screened
JANS4N23A	JANS Screened
JANS4N24A	JANS Screened

* JEDEC registered

4N22A
COLLECTOR CURRENT
VS
COLLECTOR-EMITTER VOLTAGE



4N23A
COLLECTOR CURRENT
VS
COLLECTOR-EMITTER VOLTAGE



4N24A
COLLECTOR CURRENT
VS
COLLECTOR-EMITTER VOLTAGE

